Masahiro Hori

List of Publications by Year
in descending order

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11 papers	77 citations	1684188 5 h-index	1720034 7 g-index
11 all docs	11 docs citations	11 times ranked	60 citing authors

#	Article	IF	Citations
1	Single-electron quantization at room temperature in a-few-donor quantum dot in silicon nano-transistors. Applied Physics Letters, 2017, 110, .	3.3	22
2	Analysis of electron capture process in charge pumping sequence using time domain measurements. Applied Physics Letters, 2014, 105, 261602.	3.3	17
3	Charge Pumping Under Spin Resonance in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Si</mml:mi><mml:mo stretchy="false">(</mml:mo><mml:mn>100</mml:mn><mml:mo) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 652 Td (stretchy="false	3.8	13
4	Applied, 2019, 11, . Direct observation of electron emission and recombination processes by time domain measurements of charge pumping current. Applied Physics Letters, 2015, 106, .	3.3	10
5	Electrical activation and electron spin resonance measurements of arsenic implanted in silicon. Applied Physics Letters, 2015, 106, 142105.	3.3	5
6	Improvement of charge-pumping electrically detected magnetic resonance and its application to silicon metalâ€“oxideâ€“semiconductor field-effect transistor. Applied Physics Express, 2017, 10, 015701.	2.4	5
7	Electron aspirator using electronâ€“electron scattering in nanoscale silicon. Nature Communications, 2018, 9, 4813.	12.8	5
8	Charge pumping EDMR towards charge/spin manipulation in silicon at room temperature. , 2016, , .		0
9	Detection and Characterization of Single Near-Interface Oxide Traps with the Charge Pumping Method. , 2018, , .		0
10	Detection of arsenic donor electrons using gate-pulse-induced spin-dependent recombination in silicon transistors. Applied Physics Letters, 2021, 118, 263504.	3.3	0
11	Critical conductance of two-dimensional electron gas in silicon-on-insulator metal-oxide-semiconductor field-effect transistor. Applied Physics Express, 2021, 14, 104003.	2.4	0